

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings of claims in the application:

LISTING OF CLAIMS:

Claims 1-45 (Canceled)

46. (Currently Amended) A semiconductor device comprising:

a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;

a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip:

a base resin film formed on the main surface of the semiconductor chip and having a plurality of electrode holes formed therein, the base resin film having a first surface facing the main surface of the semiconductor chip, a second surface opposite to the first surface and a through hole provided thereof;

a plurality of conductive patterns formed on the first surface of the base resin film, the conductive patterns extending near the through hole; and

an insulating film formed on the first surface of the base resin film and the conductive patterns, ~~the base resin having a plurality of electrode holes for exposing a part of the conductive patterns~~ ;wherein the conductive patterns extending in the through hole are connected with the electrodes and a plurality of electrodes holes exposing a part of the conductive patterns.

47. (Previously presented) A semiconductor device according to claim 46, wherein the main surface and side surface of the semiconductor chip are covered by molding resin.

48. (Previously presented) A semiconductor device according to claim 46, further comprising a plurality of solder balls formed on the electrode holes.

49. (Previously presented) A semiconductor device according to claim 46, wherein the base resin film is formed on the main surface, back surface and side surfaces of the semiconductor chip.

50. (Previously presented) A semiconductor device according to claim 46, wherein the base resin film is covered by elastic resin.

51. (Previously presented) A semiconductor device according to claim 50, wherein the elastic resin is polyimide.

52. (Currently Amended) A semiconductor device comprising:

a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;

a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip;

a base resin film formed on the main surface of the semiconductor chip, the base resin film having a

first surface facing said semiconductor chip, a second surface opposite to the first surface, ~~and a~~

through hole and a plurality of electrode holes provided thereof;

a plurality of conductive patterns formed on the second surface of the base resin film, the conductive patterns extending near the through hole;

an insulating film formed on the second surface of the base resin film and conductive patterns, ~~the~~
~~base resin having a plurality of electrode holes for exposing a part of the conductive patterns,~~
wherein the conductive patterns extending in the through hole are connected with the electrodes and
a plurality of electrode holes exposing a part of the conductive patterns.

53. (Previously presented) A semiconductor device according to claim 52, wherein the main surface and side surface of the semiconductor chip are covered by molding resin.

54. (Previously presented) A semiconductor device according to claim 52, further comprising a plurality of solder balls formed on the electrodes holes.

55. (Previously presented) A semiconductor device according to claim 52, wherein the base resin film is formed on the main surface, back surface and the side surfaces of the semiconductor chip.

56. (Previously presented) A semiconductor device according to claim 52, wherein the base resin film is covered by elastic resin.

57. (Previously presented) A semiconductor device according to claim 56, wherein the elastic resin is polyimide.

58. (Currently Amended) A semiconductor device comprising:

a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;
a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip;
a base resin film formed on the main surface of the semiconductor chip, the base resin film having a first surface facing said semiconductor chip and a second surface opposite the first surface and having a plurality of second electrode holes;
a plurality of electrode patterns formed on the first surface of the base resin film;
a first insulating film formed on the first surface of the base resin film, the first insulating film having a plurality of first electrode holes for exposing the electrode patterns;
a plurality of conductive patterns formed on the second surface of the base resin film, the conductive patterns electrically connected to the electrode patterns; and
a second insulating film formed on the second surface of the base resin film and the conductive patterns, ~~base resin having a plurality of~~ wherein the second electrode holes ~~for exposing~~ expose a part of the conductive patterns.

59. (Previously presented) A semiconductor device according to claim 58, wherein the main surface and the side surface of the semiconductor chip are covered by molding resin.

60. (Previously presented) A semiconductor device according to claim 58, further comprising a plurality of solder balls formed on the second electrodes holes.

61. (Previously presented) A semiconductor device according to claim 58, wherein the base resin film is formed on the main surface, back surface and the side surfaces of the semiconductor chip.

62. (Previously presented) A semiconductor device according to claim 61, wherein the base resin film is substantially surrounding the semiconductor chip.

63. (Previously presented) A semiconductor device according to claim 58, wherein the base resin is covered by elastic resin.

64. (Previously presented) A semiconductor device according to claim 63, wherein the elastic resin is polyimide.